

**Amendments to the Claims**

Claims 1-39 (cancelled).

Claim 40 (previously presented): A method of forming conductive lines, comprising:

forming an oxide isolation grid between silicon structures, at least a portion of the grid surrounding the lateral edges of at least one of the structures, wherein an upper portion of the one of the structures is bare;

forming conductive material within the oxide isolation grid to form a conductive grid therein; and

removing selected portions of the conductive grid to define interconnect lines within the oxide isolation grid.

Claim 41 (previously presented): The method of forming conductive lines of claim 40, wherein the forming the oxide isolation grid comprises forming individual oxide isolation regions over a silicon substrate by trench and refill technique.

Claim 42 (previously presented): The method of forming conductive lines of claim 40, wherein:

the silicon structures comprise silicon-containing islands, the islands being formed over an insulative surface; and

the forming the oxide isolation grid comprises forming oxide isolation regions between silicon-containing islands.

Claim 43 (previously presented): The method of forming conductive lines of claim 40, wherein the forming the conductive material within the oxide isolation grid comprises:

etching into the oxide isolation grid to define a network of outwardly-exposed trenches running within the oxide isolation grid;

forming conductive material within and over the outwardly-exposed trenches to a degree sufficient to completely fill the trenches; and

planarizing the conductive material to isolate conductive material within the trenches and to define the conductive grid.